

S/N 09/866,938

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble et al.

Examiner: Unknown

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Group Art Unit: 2813

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Docket: 303.330US3

Title: ULTRA HIGH DENSITY FLASH MEMORY

#6/B
4/10/02
Harris

SUPPLEMENTAL PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Before taking up the above-identified application for examination, please enter the following amendments.

IN THE CLAIMS

Please cancel claims 42-44 and add the following new claims:

45. (New) The method of claim 41, wherein the method further includes:
- forming a thin silicon nitride oxidation barrier layer by chemical vapor deposition on the sidewall regions of the second troughs;
 - anisotropically etching the thin silicon nitride oxidation barrier layer to expose bottom portions of the second troughs;
 - forming a bottom insulation layer on the bottom portions of the second troughs by thermal oxidation; and
 - stripping the thin silicon nitride oxidation barrier layer from the sidewall regions of the second troughs by a brief phosphoric acid etch.
46. (New) A method comprising:
- forming a first source/drain layer at a surface of a substrate;
 - forming a second source/drain layer at a surface of an epitaxial layer, the epitaxial layer being formed on the first source/drain layer and comprising P- silicon;
 - forming a thin layer of silicon dioxide on the second source/drain layer;
 - forming a layer of silicon nitride on the thin layer of silicon dioxide;

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02 FC:102